

IN THE SPECIFICATION:

**Page 3, paragraph 3, please replace with the following:**

An inventive semiconductor memory device includes a memory cell capacitor for storing data thereon. The capacitor is made up of a first electrode or lower electrode connected to a contact plug, a second electrode or upper electrode and a capacitive insulating film interposed between the first and second electrodes. The first electrode includes a first barrier film or first film of the lower electrode in contact with the contact plug and a second barrier film or second film of the lower electrode, which is formed on the first barrier film and prevents the diffusion of oxygen. The second barrier film covers the upper and side faces of the first barrier film.

**Page 4, paragraph 6, please replace with the following:**

Another inventive semiconductor memory device includes a memory cell capacitor for storing data thereon. The capacitor is made up of a first electrode connected to a contact plug, a second electrode and a capacitive insulating film interposed between the first and second electrodes. The first electrode includes a first barrier film in contact with the contact plug, a second barrier film covering the upper surface of the first barrier film and a third barrier film or third film of the lower electrode covering the side faces of the first barrier film. The second and third barrier films prevent the diffusion of oxygen.

**Page 8, paragraph 3, please replace with the following:**

The memory cell capacitor 2 is made up of lower and upper electrodes 8 and 12 and a capacitive insulating film 9 interposed between the electrodes 8 and 12. The lower electrode 8 consists of first and second barrier films or first and second films of the lower electrode 6 and 7.

**Page 8, paragraph 4, please replace with the following:**

The first barrier film or first film of the lower electrode 6 has a multilayer structure including Ti, TiAlN and Ir films stacked in this order. The Ir, TiAlN and Ti films have thicknesses of 100 nm, 40 nm and 20 nm, respectively.

**Page 8, paragraph 5, please replace with the following:**

The second barrier film or second film of the lower electrode 7 has a multilayer structure including IrO<sub>2</sub> and Pt films stacked in this order. And the second barrier film 7 is deposited so as to cover the first barrier film 6 completely. The Pt and IrO<sub>2</sub> films have thicknesses of 50 nm and 150 nm, respectively. Particularly, the IrO<sub>2</sub> film preferably has a thickness between 70 nm and 250 nm.

**Page 15, paragraph 2, please replace with the following:**

The first barrier film 26 is made up of a multilayer structure 26a or first film of the lower electrode, including Ti and TiAlN films stacked in this order, and another multilayer structure 26b or the second film of the lower electrode, including Ir, IrO<sub>2</sub> and Pt films stacked in this order. The Pt, IrO<sub>2</sub>, Ir, TiAlN and Ti films have thicknesses of 50 nm, 80 nm, 100 nm, 40 nm and 20 nm, respectively.

**Page 15, paragraph 3, please replace with the following:**

The second barrier film or third film of the lower electrode 27 is made of IrO<sub>2</sub> and is deposited so as to cover the side faces of the first barrier film 26 completely. The IrO<sub>2</sub> film has a thickness of 150 nm. Particularly, the IrO<sub>2</sub> film preferably has a thickness between 70 nm and 250 nm.